Monolithic Linear IC

SANYO

LA1175, 1175M

FM Front End For Car Radio, Home Stereo Applications

Functions

• Double-balanced type MIX, PIN diode drive AGC output, MOS FET gate drive AGC output, keyed AGC, differential IF amplifier, buffer amplifier for oscillation, local oscillation.

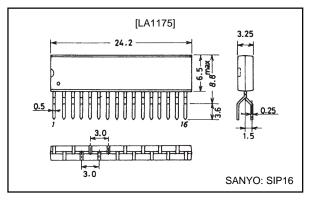
Features

- By using the keyed AGC system, which is effective in improving the sensitivity suppression characteristic, in combination with the antenna damping AGC (PIN diode driver on chip) and MOS FET 2nd gate drive AGC, the intermodulation characteristic for a large undesired signal is greatly improved. It is also possible to use the keyed AGC system in combination with the antenna damping AGC or MOS FET 2nd gate drive AGC.
- The temperature characteristic and noise figure are improved. The same supply voltage makes it easy to use the LA1175, 1175M.

Package Dimensions

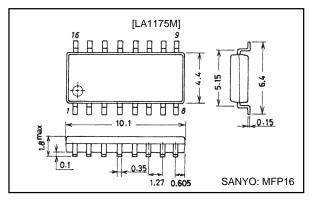
unit: mm

3020A-SIP16



unit: mm

3035A-MFP16



Specifications Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
			8	
Maximum supply voltage	V _{CC} max	Pins 4, 14	9.5	V
		Pins 8, 9	15	V
Allowable power dissipation	Pd max	LA1175 : Ta≤70°C	460	mW
		LA1175M : Ta≤70°C	435	mW
		Mounted on PCB (bakelite)		
		of 40mm×48mm×1.8mm ²		
Operating temperature	Topr		-20 to +70	°C
Storage temperature	Tstg		-40 to +125	°C

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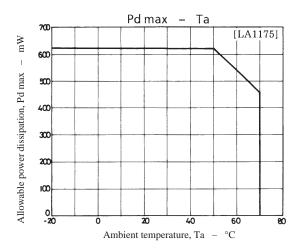
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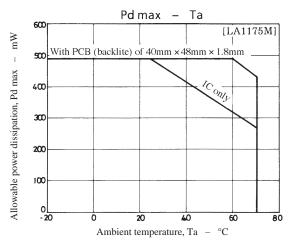
Operating Conditions at Ta=25°C

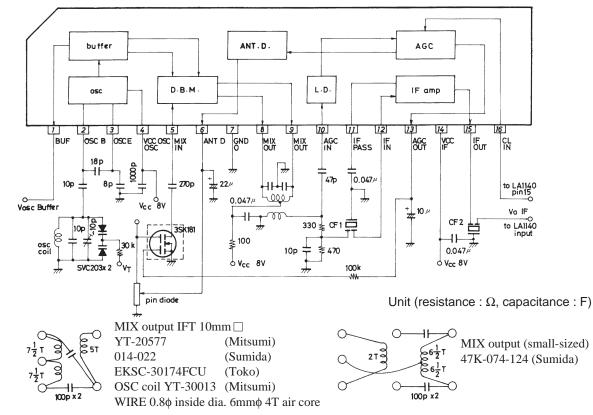
Parameter	Symbol	Conditions	Ratings	Unit
Recommended supply voltage	Vcc	Pin 4, 8, 9, 14	8	V
Operating voltagerange	V _{CC} op		8 to 9	V

Electrical Characteristics at Ta=25°C, V_{CC}=8V, See specified Test Circuit.

Parameter	Symbol	Conditions	Ratings			Unit
Tarameter Symbo		Conditions	min	typ	max	Onit
Current drain	ICC	Pins 4, 8, 9, 14 : no input	23.0	28.0	33.0	mA
AGC high-level voltage	V _{AGCH}	V _{IN} =0dBµ, V _{CL} =4V	7.6	7.9		V
AGC low-level voltage	V _{AGCL}	V_{IN} =100dB μ , V_{CL} =4V		0.2	0.7	V
IF input resistance	R _{IN}		260	330	400	Ω
AGC control input	V _{CL} 7	V _{IN} =100dBµ, V _{AGC} =7V		0.25	0.5	V
	V _{CL} 2	VIN=100dBµ, VAGC=2V	1.1	1.6	2.1	V
Voltage gain	Av	LA1175 : V _{IN} =75dBµ	99	102	105	dBµ
		LA1175M : V _{IN} =75dBµ	97	100	103	dBµ
Input limiting voltage	V _{INlim}	LA1175 : Referenced to VIN=110dBµ	81	88	95	dBµ
		LA1175M : Referenced to V_{IN} =110dBµ	80	87	94	dBµ
AGC input voltage	ViAGC	V _{AGC} =2V	67	74	81	dBµ
Saturation output voltage	Vout	LA1175 : V _{IN} =110dBµ	110	114		dBµ
		LA1175M : V _{IN} =110dBµ	100	113		dBµ
OSC BUFF output	VOSC BUFF	1kΩ load	105	109		dBµ
ANT damping drive	I _{ANT-D}	V _{IN} =100dBµ	4.5	6.0	8.0	mA
current						

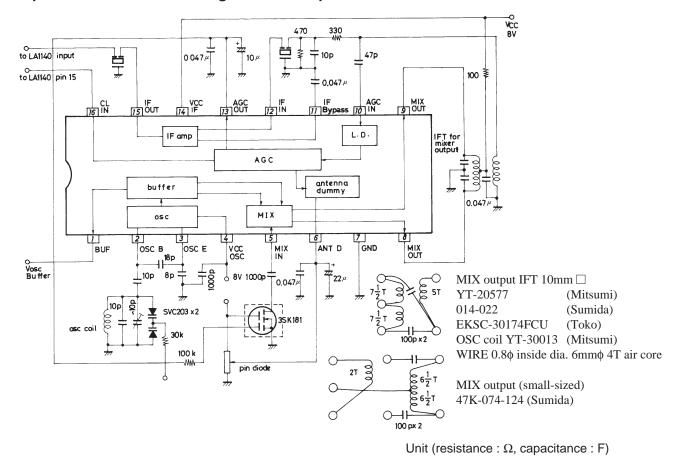


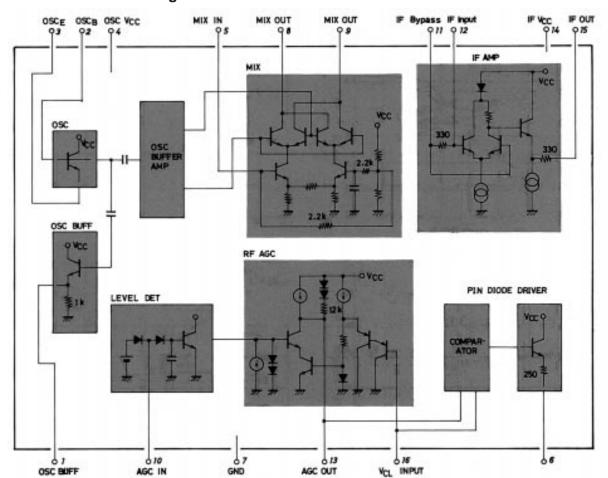




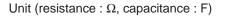
Equivalent Circuit Block Diagram and Peripheral Circuit : LA1175

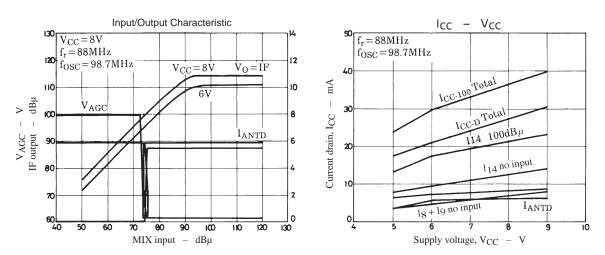
Equivalent Circuit Block Diagram and Peripheral Circuit : LA1175M

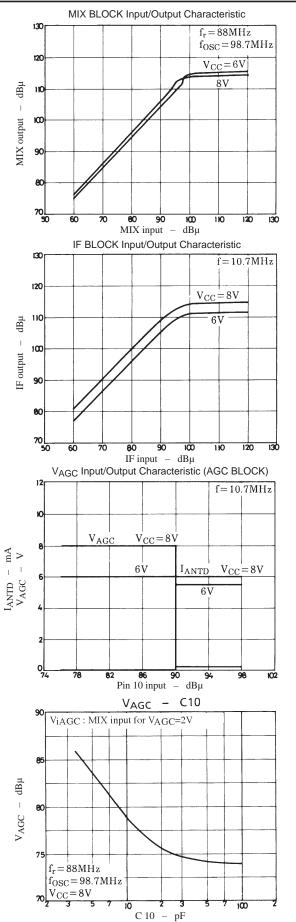


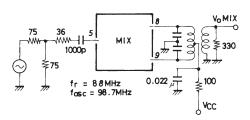


Internal Connection Diagram : LA1175

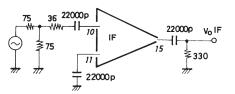


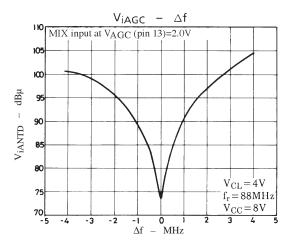


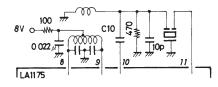




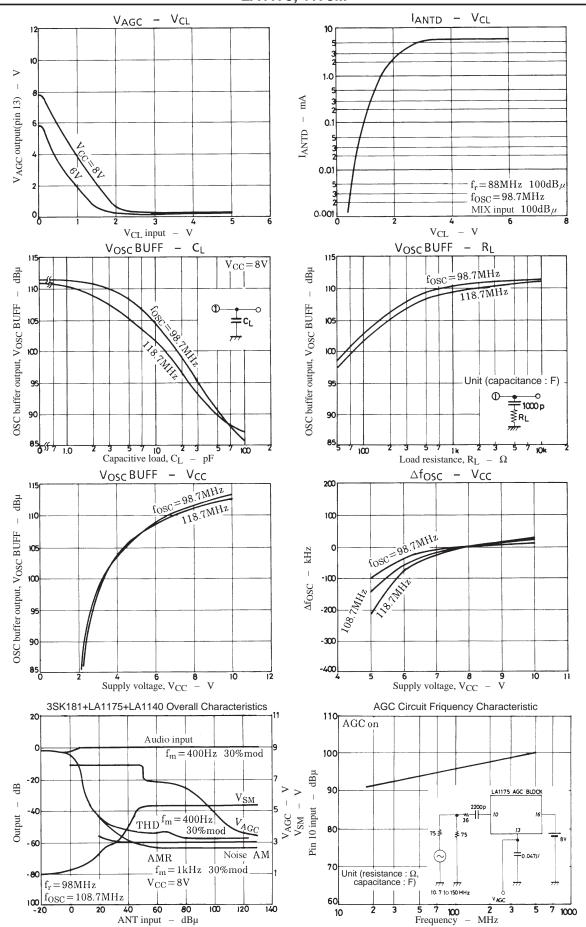
Unit (resistance : Ω , capacitance : F)

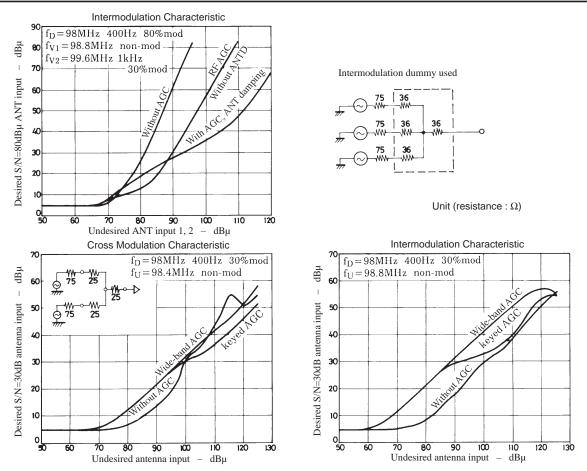






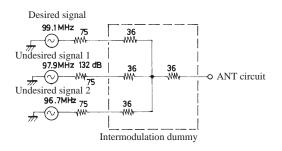






Improvement of IM characteristic in strong undesired input signal mode when ANT damping AGC is used (LA1174). Test conditions

- f_D : 99.1MHz, f_m =400Hz 100% mod
- $f_{U1}\ :97.9 MHz$ non-mod SG open $132 dB\mu$
- f_{U2} : 96.7MHz f_m =1kHz 100% mod



Unit (resistance : Ω)

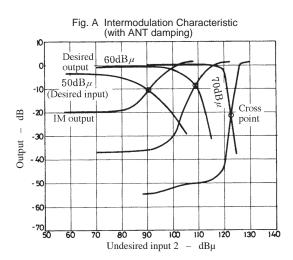
Cross point

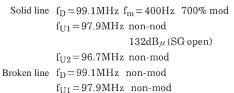
The open input level of undesired signal 2 at which the IM output and desired signal output are at the same level.

IM output

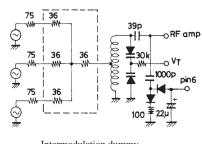
- : Non-mod at each specified input
- Desired signalUndesired signal 1
 - al 1 : Non-mod at input 132dBµ (SG open)
 - Undesired signal 2 : 100% mod with input variable
- Desired signal output Desired signal
- : 100% at each specified input
- Undesired signal 1
 - 1 : Non-mod at input 132dBµ (SG open)
 - Undesired signal 2 : Non-mod with input variable

	Desired input level	50dBµ	60dBµ	70dBµ	80dBµ	
point	With ANT damping RF AGC and ANTD AGC	90.5dBµ	109dBµ	123dBµ	Test impossible	Refer to Fig. A.
Cross	Without ANT damping RF AGC only	59.5dBµ	72dBµ	89dBµ	98dBµ	Refer to Fig. B.
	Improvement	31dB	37dB	34dB		

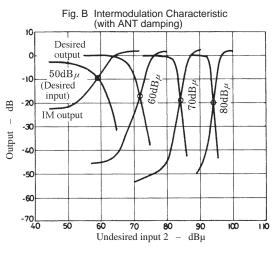




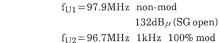
 $132 dB_{\mu}$ (SG open) f_{U2}=96.7MHz 1kHz 100% mod

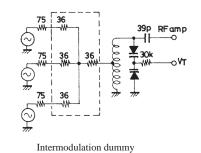


Intermodulation dummy

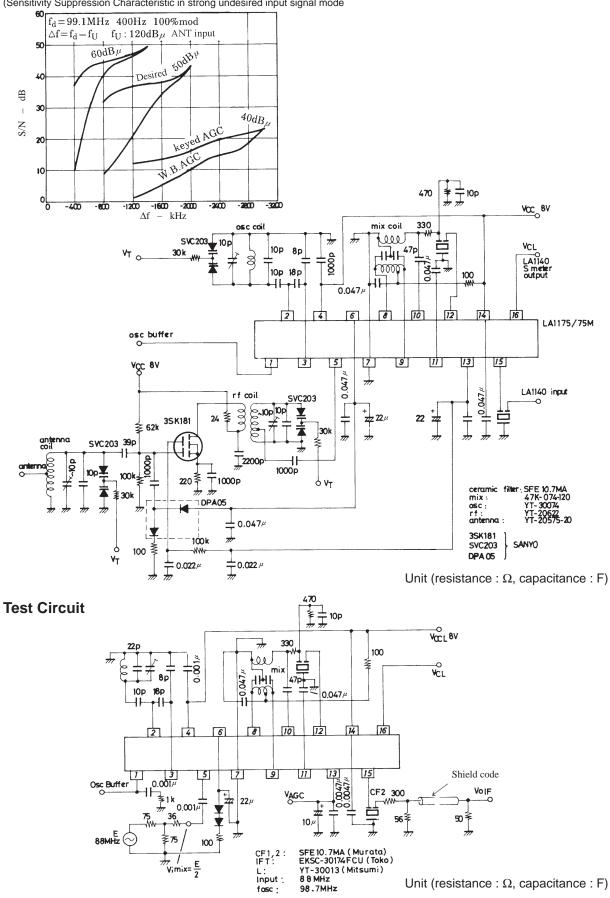


Solid line $f_D = 99.1 MHz f_m = 400 Hz 700\% mod$ $f_{U1} = 97.9 MHz non-nod$ $132 dB_{\mu} (SG open)$ $f_{U2} = 96.7 MHz non-mod$ Broken line $f_D = 99.1 MHz non-mod$

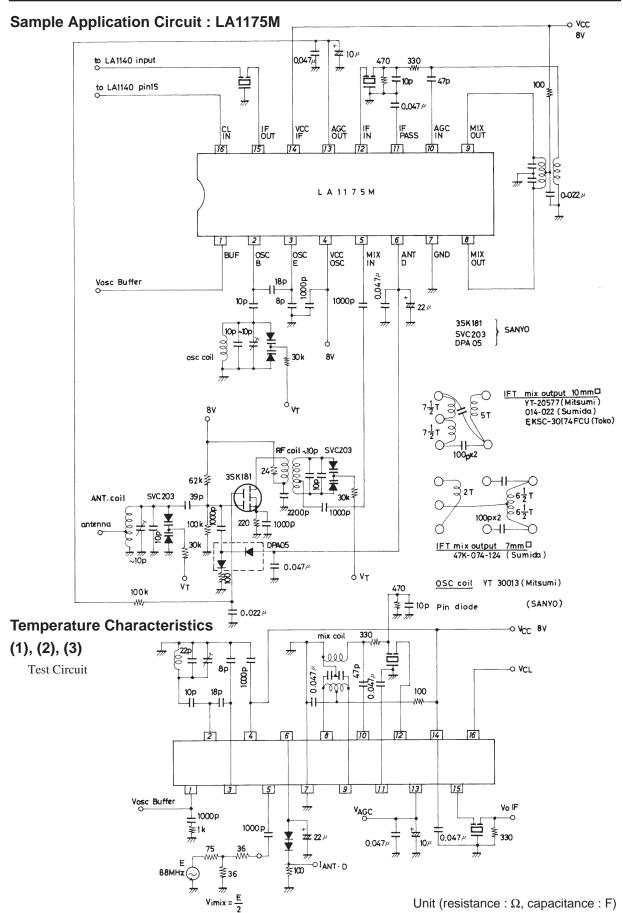


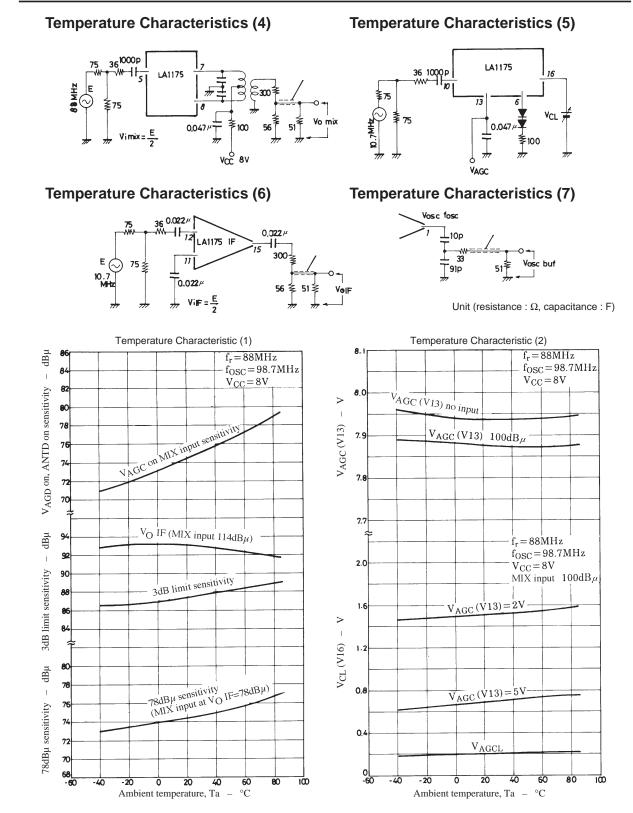


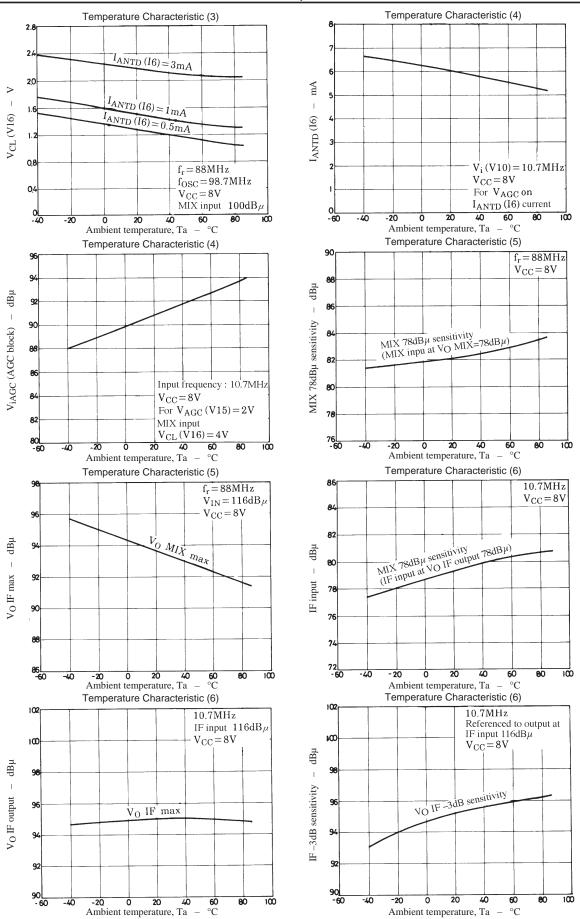
Unit (resistance : Ω , capacitance F)

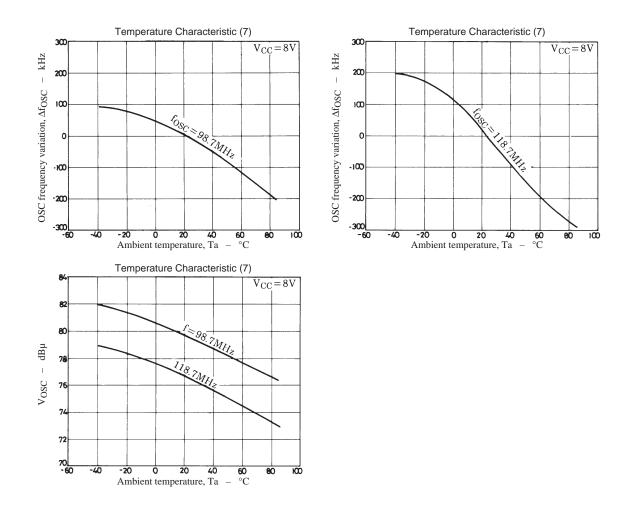


3SK181+LA1175+LA1140 Cross Modulation Characteristic (Sensitivity Suppression Characteristic in strong undesired input signal mode









Description of AGC circuit in the LA1175, 1175M

The LA1175, 1175M are designed so that AGC is operated in the order shown below.

ANT damping (PIN diode) → MOS FET 2nd gate voltage control

(Attenuation)20dB (Attenuation)60dB

The following are the reasons why AGC is operated in this order.

- (1) When a signal of 110dBµ or greater is applied to the varactor in the ANT circuit, intermodulation may occur. In this case, if AGC is operated in the order of MOS FET 2nd gate control AGC → ANT damping (PIN diode), the input to the varactor in the ANT circuit is not restricted unless a strong signal with AGC attenuation 60dB or greater is given. Therefore, AGC should be operated in the order shown above.
- (2) If the two AGC loops (AGC loop (ANT damping) and AGC loop (MOS FET 2nd gate control)) are operated simultaneously, the transient response of AGC loses stability. Therefore, the order shown below is impracticable.

MOS FET 2nd gate control \rightarrow ANT damping \rightarrow MOS FET 2nd gate control.

Relation between keyed AGC and two AGC loops

For the LA1170, keyed AGC provides AGC attenuation control (RF MOS FET 2nd gate). For the LA1175, 1175M, however, there are two AGC loops as shown above. Therefore, keyed AGC must be applied to both of the two AGC loops. The LA1175, 1175M contain the ANT damping circuit to improve intermodulation in a strong field, but the prevention of intermodulation in a strong field and the improvement of the sensitivity suppression characteristic by keyed AGC are mutually exclusive as mentioned below.

Conditions Desired signal

Undesired signals 1, 2

Weak field

Strong field (Field strength in which the ANT circuit may cause intermodulation to occur)

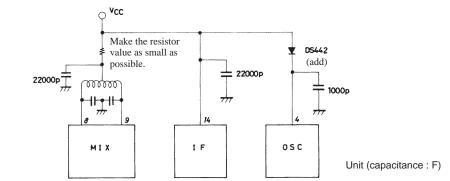
If keyed AGC is operated to cause AGC-OFF mode to be entered when a desired signal is received, the varactor in the ANT circuit may be distorted and intermodulation may occur, which means that it is meaningless for the LA1175, 1175M to contain the ANT damping circuit because it produces no effect. Therefore, the effect of the keyed AGC circuit in the LA1175, 1175M on the ANT damping circuit is made less than that in the LA1170 so that the abovementioned problem does not arise. However, if the LA1175, 1175M are used under the same conditions as for the LA1170 (no ANT damping, pin 6 open), keyed AGC is operated in the same manner as for the LA1170.

Application circuit used in a very strong field

Since the LA1175, 1175M are designed to be operated from single supply, the dynamic range of the MIX output becomes narrower as compared with the dual-supply type (V_{CC} MIX=12V, other=8V) heretofore in use. IF an adjacent interference channel signal is very strong, the intermodulation characteristic at Δf =400kHz is deteriorated, because the dynamic range of the MIX output exceeds the limit, which causes a distortion to occur. The following three countermeasures are available.

1. Q of the MIX coil is made higher to provide a higher selectivity.

- (Must be balanced with the detection band of the wide-band AGC)
- 2. The LA1175, 1175M are operated from dual supplies (Most ideal).
- 3. The application circuit shown below is used.



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